

Application No.: 10/617,833**Docket No.: 2336-194****AMENDMENTS TO THE SPECIFICATION:**

Please amend the paragraph on page 4, beginning at line 14 as follows:

In order to solve this problem generated by the nonsymmetrical structure of the conventional semiconductor laser device, the refractivity of the second guide layer 6 disposed on the opposite side of the n-type clad layer 9 with high refractivity is heightened, or the thickness or band gap of the second guide layer 6 is increased more than that of the first guide layer 8.

Please amend the paragraph on page 20, beginning at line 14 as follows:

As shown in Table [[1]]2, a semiconductor laser device was designed and manufactured so that it has a FFV value of 17°, by a method similar to that for manufacturing the semiconductor laser device shown in Figs. 5a and 5b.

Please amend the paragraph on page 21, beginning at line 2 as follows:

As shown in Table [[2]]1, a conventional semiconductor laser device was designed and manufactured so that it has a FFV value of 17°, by the conventional method for increasing the refractivity of a lower clad layer and the thickness of an upper guide layer.

Abstract:

Please replace the current Abstract with the following replacement/new Abstract